

In the Claims

CLAIMS

Claims 1-26 (canceled).

27. (Currently amended) A method of forming integrated circuitry, comprising:

forming LOCOS field oxide by providing nitride masking blocks over a silicon substrate; the nitride masking blocks being separated by spaces that are less than or equal to 0.25 micron; the spaces leaving portions of the ~~underlying semiconductor~~ silicon substrate exposed between the nitride masking blocks; subjecting the silicon substrate to dry oxidation to form LOCOS field oxide configured to provide isolation within the spaces and then removing the nitride masking blocks; and

forming an array of memory cells in lines over the ~~semiconductive~~ silicon substrate and occupying area thereover, the respective area consumed by at least some individual memory cells within the array being less than $8F^2$, where "F" is no greater than 0.25 micron and is defined as equal to one-half of minimum pitch, with minimum pitch being defined as equal to the smallest distance of a line width plus width of a space immediately adjacent said line on one side of said line between said line and a next adjacent line in a repeated pattern within the array; at least some of the minimum pitch adjacent lines of memory cells within the array being isolated from one another by the LOCOS field oxide.

28. (Previously presented) The method of claim 27 wherein the lines of memory cells are substantially straight throughout the array.

29. (Previously presented) The method of claim 27 wherein the LOCOS field oxide between adjacent lines is formed to be less than or equal to 2500 Angstroms thick.

30. (Previously presented) The method of claim 27 wherein said respective area consumed by at least some individual memory cells within the array is no greater than about $7F^2$.

31. (Previously presented) The method of claim 27 wherein said respective area consumed by at least some individual memory cells within the array is no greater than about $6F^2$.

32. (Previously presented) The method of claim 27, wherein forming an array of memory cells in lines comprises forming an array of memory cells coupled to an array of word lines and bit lines, wherein the bit lines are formed to comprise D and D* lines arranged in a folded bit line architecture within the array.

33. (Previously presented) The method of claim 27, wherein forming an array of memory cells in lines comprises forming an array of memory cells coupled to an array of word lines and bit lines, wherein the bit lines are orthogonal to the word lines.

34. (Currently amended) A method of forming memory integrated circuitry, comprising:

forming LOCOS field oxide by providing nitride masking blocks over a silicon substrate; the nitride masking blocks being separated by spaces that are less than or equal to 0.25 micron; the spaces leaving portions of the ~~underlying semiconductor~~ silicon substrate exposed between the nitride masking blocks; subjecting the silicon substrate to dry oxidation to form LOCOS field oxide configured to provide isolation within the spaces and then removing the nitride masking blocks; and

forming an array of memory cells over the ~~semiconductive~~ silicon substrate and occupying area thereover, at least some memory cells of the array being formed in lines of active area formed within the ~~semiconductive~~ silicon substrate which are continuous between adjacent memory cells, said adjacent memory cells being isolated from one another relative to the continuous active area formed therebetween by a conductive line formed over said continuous active area between said adjacent memory cells; the respective area consumed by individual ones of said adjacent memory cells being less than $8F^2$, where "F" is no greater than 0.25 micron and is defined as equal to one-half of minimum pitch, with minimum pitch being defined as equal to the smallest distance of a line width plus width of a space immediately adjacent said line on one side of said line between said line and a next adjacent line in a repeated pattern within the array; at least some of the minimum pitch adjacent lines of memory cells within the array being isolated from one another by the LOCOS field oxide.

35. (Previously presented) The method of claim 34, wherein forming an array of memory cells comprises forming an array of memory cells coupled to an array of word lines and bit lines, wherein the bit lines are formed to comprise D and D* lines arranged in a folded bit line architecture within the array.

36. (Previously presented) The method of claim 34, wherein forming an array of memory cells comprises forming an array of memory cells coupled to an array of word lines and bit lines, wherein the bit lines are not parallel to the word lines.

37. (Previously presented) The method of claim 36, wherein the bit lines comprise a folded bit line architecture within the array.

38. (Currently amended) A method of forming dynamic random access memory circuitry, comprising:

forming LOCOS field oxide by providing nitride masking blocks over a silicon substrate; the nitride masking blocks being separated by spaces that are less than or equal to 0.25 micron; the spaces leaving portions of the ~~underlying semiconductor~~ silicon substrate exposed between the nitride masking blocks; subjecting the silicon substrate to dry oxidation to form LOCOS field oxide configured to provide isolation within the spaces and then removing the nitride masking blocks;

forming an array of word lines and bit lines over the ~~semiconductive~~ silicon substrate to define an array of DRAM cells occupying area over the ~~semiconductive~~ silicon substrate, at least some DRAM cells of the array being formed in lines of active area formed within the ~~semiconductive~~ silicon substrate beneath the word lines and which are continuous between adjacent DRAM cells, said adjacent DRAM cells being isolated from one another relative to the continuous active area formed therebetween by a conductive line formed over said continuous active area between said adjacent DRAM cells; the respective area consumed by individual ones of said adjacent memory cells being less than $8F^2$, where "F" is greater than 0 micron and no greater than 0.25 micron and is defined as equal to one-half of minimum pitch, with minimum pitch being defined as equal to the smallest distance of a line width plus width of a space immediately adjacent said line on one side of said line between said line and a next adjacent line in a repeated pattern within the array; at least some of the

minimum pitch adjacent lines of memory cells within the array being isolated from one another by the LOCOS field oxide; and

wherein the bit lines are formed to comprise D and D* lines arranged in a folded bit line architecture within the array.

39. (Previously presented) The method of claim 38, wherein forming an array of word lines and bit lines comprises forming the bit lines and the word lines to be orthogonal.

40. (Currently amended) A method of forming dynamic random access memory circuitry, comprising:

forming LOCOS field oxide by providing nitride masking blocks over a semiconductor substrate; the nitride masking blocks being separated by spaces that are less than or equal to 0.25 micron; the spaces leaving portions of the ~~underlying~~ semiconductor substrate exposed between the nitride masking blocks; subjecting the semiconductor substrate to dry oxidation to form LOCOS field oxide configured to provide isolation within the spaces and then removing the nitride masking blocks;

forming an array of word lines and bit lines over the ~~bulk-silicon~~ ~~semiconductive~~ semiconductor substrate to define an array of DRAM cells occupying area over the ~~semiconductive~~ semiconductor substrate, the word lines and bit lines having respective conductive widths which are greater than 0 micron and less than or equal to 0.25 micron, the DRAM cells within the array being formed in lines of active area formed within the ~~silicon~~ semiconductor substrate beneath the word lines and which are continuous between adjacent DRAM cells, said adjacent DRAM cells being isolated from one another relative to the continuous active area formed therebetween by respective conductive lines formed over said continuous active area between said adjacent DRAM cells; at least some adjacent lines of continuous active area within the array being isolated from one another by the LOCOS field oxide, said LOCOS field oxide having a thickness of no greater than 2500 Angstroms; the respective area consumed by individual ones of said adjacent memory cells being less than 0.5 micron²; and

wherein the bit lines are formed to comprise D and D* lines arranged in a folded bit line architecture within the array.

41. (Currently amended) A method of forming dynamic random access memory circuitry, comprising:

forming LOCOS field oxide by providing nitride masking blocks over a silicon substrate; the nitride masking blocks being separated by spaces that are less than or equal to 0.25 micron; the spaces leaving portions of the ~~underlying semiconductor~~ silicon substrate exposed between the nitride masking blocks; subjecting the silicon substrate to oxidation to form LOCOS field oxide configured to provide isolation within the spaces and then removing the nitride masking blocks; and

forming an array of word lines and bit lines over the ~~semiconductive~~ silicon substrate to define an array of DRAM cells occupying area over the ~~semiconductive~~ silicon substrate, at least some DRAM cells of the array being formed in lines of active area formed within the ~~semiconductive~~ silicon substrate beneath the word lines and which are continuous between adjacent DRAM cells, said adjacent DRAM cells being isolated from one another relative to the continuous active area formed therebetween by a conductive line formed over said continuous active area between said adjacent DRAM cells; the respective area consumed by individual ones of said adjacent memory cells being less than $8F^2$, where "F" is no greater than 0.25 micron and is defined as equal to one-half of minimum pitch, with minimum pitch being defined as equal to the smallest distance of a line width plus width of a space immediately adjacent said line on one side of said line between said line and a next adjacent line in a repeated pattern within the array; at least some of the minimum pitch adjacent lines of

memory cells within the array being isolated from one another by the LOCOS field oxide.

42. (Previously presented) The method of claim 41, wherein forming an array of word lines and bit lines comprises forming the bit lines and the word lines to be orthogonal.

43. (Previously presented) The method of claim 41, wherein the bit lines are formed to comprise D and D* lines arranged in a folded bit line architecture within the array.